G. Device & Process Modeling, Simulation and Reliability 분과

2019년 2월 15일(금), 11:00-12:30
Room B (마루홀, 2층)

[FB2-G] Advanced Devices III : Technology & Simulation

좌장: 박정수 수석(SK하이닉스), 이정수 교수(POSTECH)

FB2-G-1 **11:00-11:15**	**RDF/LER-Induced Performance Variation-Immune Effect of Metal-Interlayer-Semiconductor Source/Drain on n-Ge Junctionless Field-Effect Transistor** Seung-Geun Jung, Mu-Yeoung Son, Hyeok Jeon, Tae-Hyun Kim, Young-Hun Shin, and Hyun-Yong Yu *Department of Electronic Engineering, Korea University*
FB2-G-2 **11:15-11:30**	**A Development of High Reliability HV ESD Power Clamp for Large Display Driver Ics** Wonsuk Park, Jungwoo Han, Jowoon Lee, Youngchul Kim, and Joontae Jang *Department of Electronic Engineering, DB HiTek*
FB2-G-3 **11:30-11:45**	**Domain Wall Dynamics for Transient NC Effect in Ferroelectric $BaTiO_3$ Thin Films** Hyeon Woo Park[1,2], Yong Bin Lee[1,2], Jangho Roh[1,2], Keum Do Kim[1,2], Young Hwan Lee[1,2], Seung Dam Hyun[1,2], Baeksu Kim[1,2], Ho Hyeon Kim[1,2], Beom Yong Kim[1,2], Taehwan Moon[1,2], and Cheol Seong Hwang[1,2] *[1]Department of Material Science and Engineering, Seoul National University,* *[2]Inter-University Semiconductor Research Center, Seoul National University*
FB2-G-4 **11:45-12:00**	**Effect of Boron and Gallium Doping on the Lattice Parameters in Si and $Si_{1-x}Ge_x$** Minhyeong Lee and Dae-Hong Ko *Department of Materials Science and Engineering, Yonsei University*
FB2-G-5 **12:00-12:15**	**Analytical Model of Static I-V and Flicker Noise for Tunnel Field-Effect Transistors** Young-Hun Park[1], Hyeong-Sub Song[2], Dong-Hwan Lim[3], Chang-Hwan Choi[3], Hi-Deok Lee[2], and Ji-Woon Yang[1] *[1]Department of Electronic & Information Engineering, Korea University,* *[2]Department of Electronic Engineering, Chungnam National University,* *[3]Division of Mater. Sci. and Engineering, Hanyang University*
FB2-G-6 **12:15-12:30**	**Performance Improvement of Low Frequency Noise Characteristics in Gate-Last FDSOI Tunneling Field Effect Transistor with Deuterium Passivation** Hyeong-Sub Song[1], So-Yeong Kim[1], Sung-Kyu Kwon[1], Hyun-Dong Song[1], Gawon Lee[1], Dong-Hwan Lim[2], Chang-Hwan Choi[2], and Hi-Deok Lee[1] *[1]Department of Electronics Engineering, Chungnam National University,* *[2]Division of Materials Science and Engineering, Hanyang University*